MSKSEMI 美森科













ESD

TVS

TSS

MOV

GDT

PLED

L293D-L293DD(MS)

Product specification







DESCRIPTION

The Device is a monolithic integrated high volt-age, high current four channel driver designed to accept standard DTL or TTL logic levels and drive inductive loads (such as relays solenoides, DC and stepping motors) and switching power tran- sistors. To simplify use as two bridges each pair of chan-nels is equipped with an enable input. A separate supply input is provided for the logic, allowing op-eration at a lower voltage and internal clamp di-odes are included.

This device is suitable for use in switching appli-cations at frequencies up to 5 kHz.

The L293D is assembled in a 16 lead plastic packaage which has 4 center pins connected to- gether and used for heatsinking

The L293DD is assembled in a 20 lead surface mount which has 8 center pins connected to- gether and used for heatsinking.

- 600mA OUTPUT CURRENT CAPABILITY PER CHANNEL
- 1.2A PEAK OUTPUT CURRENT (non repeti- tive) PER CHANNEL
- ENABLE FACILITY
- OVERTEMPERATURE PROTECTION
- LOGICAL "0" INPUT VOLTAGE UP TO 1.5 V (HIGH NOISE IMMUNITY)
- INTERNAL CLAMP DIODES

Reference News

PACKAG	EOUTLINE	Ма	rking
Hard Contraction		MSKSEMI L293DD MS****	MSKSEMI L293D MS****
SOP-20	DIP-16	SOP-20	DIP-16

ordering information

P/N	PKG	QTY
L293DD(MS)	SOP-20	1000/tray
L293D(MS)	DIP-16	25/One tube 1000/a box of



BLOCK DIAGRAM



ABSOLUTEMAXIMUMRATINGS

Symbol	Parameter	Value	Unit
Vs	Supply Voltage	36	V
V _{SS}	Logic Supply Voltage	36	V
Vi	Input Voltage	7	V
Ven	Enable Voltage	7	V
lo	Peak Output Current (100 µs non repetitive)	1.2	А
Ptot	Total Power Dissipation at T_{pins} = 90 $^\circ C$	4	W
Tstg,Tj	Storage and Junction Temperature	– 40 to 150	Ĉ



PIN CONNECTIONS (Top view)



THERMAL DATA

Symbol	Decription	DIP	SO	Unit
Rth j-pins	Thermal Resistance Junction-pins max.	_	14	°C/W
Rth j-amb	Thermal Resistance junction-ambient max.	80	50 (*)	°C/W
Rth j-case	Thermal Resistance Junction-case max.	14	-	

(*) With 6sq. cm on board heatsink.



ELECTRICAL CHARACTERISTICS (for each channel, VS =24V, VSS =5 V, Tamb = 25°C, unless

otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Vs	Supply Voltage (pin 10)		Vss		36	V
Vss	Logic Supply Voltage (pin 20)		4.5		36	V
		$V_i = L$; $I_0 = 0$; $V_{en} = H$		2	6	mA
ls	Total Quiescent Supply Current (pin 10)	$V_i = H ; I_0 = 0 ; V_{en} = H$		16	24	mA
		V _{en} = L			4	mA
	T () O () O ()	$V_i = L$; $I_0 = 0$; $V_{en} = H$		44	60	mA
lss	Total Quiescent Logic Supply Current (pin 20)	$V_i = H$; $I_0 = 0$; $V_{en} = H$		16	22	mA
		Ven = L		16	24	mA
VIL	Input Low Voltage (pin 2, 9, 12, 19)		- 0.3		1.5	V
	Input High Voltage (pin 2, 9,	V _{SS} < 7 V	2.3		V _{SS}	V
VIH	12, 19)	V _{SS} > 7 V	2.3		7	V
IIL	Low Voltage Input Current (pin 2, 9, 12, 19)	V _{IL} = 1.5 V			- 10	μA
I _{IH}	High Voltage Input Current (pin 2, 9, 12, 19)	2.3 V < V _{IH} < V _{SS} – 0.6 V		30	100	μA
Ven L	Enable Low Voltage (pin 1, 11)		- 0.3		1.5	V
	Enable High Voltage	V _{SS} < 7 V	2.3		Vss	V
Ven H	(pin 1, 11)	V _{SS} > 7 V	2.3		7	V
len L	Low Voltage Enable Current (pin 1, 11)	V _{en L} = 1.5 V		- 30	- 100	μA
I _{en H}	High Voltage Enable Current (pin 1, 11)	$2.3 V < V_{en H} < V_{SS} - 0.6 V$			± 10	μA
V _{CE(sat)} H	Source Output Saturation Voltage (pins 3, 8, 13, 18)	lo = - 0.6 A		1.4	1.8	V
VCE(sat)L	Sink Output Saturation Voltage (pins 3, 8, 13, 18)	I ₀ = + 0.6 A		1.2	1.8	V
VF	Clamp Diode Forward Voltage	I ₀ = 600nA		1.3		V
tr	Rise Time (*)	0.1 to 0.9 V _o		250		ns
t _f	Fall Time (*)	0.9 to 0.1 V _O		250		ns
ton	Turn-on Delay (*)	0.5 V _i to 0.5 V _o		750		ns
toff	Turn-off Delay (*)	0.5 V _i to 0.5 V _o		200		ns

(*) See fig. 1.



TRUTH TABLE (one channel)

Input	Enable (*)	Output
Н	Н	Н
L	Н	L
н	L	Z
L	L	Z

Z = High output impedance (*) Relative to the considered channel









DIM.	mm			inch		
	MIN.	ТҮР.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
В	0.85		1.40	0.033		0.055
b		0.50			0.020	
b1	0.38		0.50	0.015		0.020
D			20.0			0.787
E		8.80			0.346	
е		2.54			0.100	
e3		17.78			0.700	
F			7.10			0.280
I			5.10			0.201
L		3.30			0.130	
Z			1.27			0.050

В

b

Ζ





e







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